

# Sokrates T Pantelides

## List of Publications by Year in descending order

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411  
papers

25,055  
citations

7069

78  
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8835

145  
g-index

417  
all docs

417  
docs citations

417  
times ranked

26337  
citing authors

#	ARTICLE	IF	CITATIONS
1	Intrinsically Honeycomb-Patterned Hydrogenated Graphene. <i>Small</i> , 2022, 18, e2102687.	5.2	3
2	Unique Features of Polarization in Ferroelectric Ionic Conductors. <i>Advanced Electronic Materials</i> , 2022, 8, 2100810.	2.6	9
3	Ionic Control over Ferroelectricity in 2D Layered van der Waals Capacitors. <i>ACS Applied Materials &amp; Interfaces</i> , 2022, 14, 3018-3026.	4.0	16
4	Radiation Effects in AlGaIn/GaN HEMTs. <i>IEEE Transactions on Nuclear Science</i> , 2022, 69, 1105-1119.	1.2	32
5	Emergent interface vibrational structure of oxide superlattices. <i>Nature</i> , 2022, 601, 556-561.	13.7	40
6	Nanoscale Control of Polar Surface Phases in Layered van der Waals $\text{CuInP}_2\text{S}_6$ . <i>ACS Nano</i> , 2022, 16, 2452-2460.	7.3	12
7	Origin of insulating and nonferromagnetic $\text{SrRuO}_3$ monolayers. <i>Physical Review B</i> , 2022, 105, .	1.1	6
8	Tunable, Ferroelectricity-Inducing, Spin-Spiral Magnetic Ordering in Monolayer FeOCl. <i>Nano Letters</i> , 2022, 22, 3598-3603.	4.5	7
9	Intrinsically patterned corrals in monolayer $\text{Ag}_5\text{Se}_2$ and selective molecular co-adsorption. <i>Nano Research</i> , 2022, 15, 6730-6735.	5.8	3
10	Thermal transport of monolayer amorphous carbon and boron nitride. <i>Applied Physics Letters</i> , 2022, 120, .	1.5	3
11	Engineering the Crack Structure and Fracture Behavior in Monolayer $\text{MoS}_2$ By Selective Creation of Point Defects. <i>Advanced Science</i> , 2022, 9, .	5.6	10
12	The Diffusion Mechanism of Ge During Oxidation of Si/SiGe Nanofins. <i>ACS Applied Materials &amp; Interfaces</i> , 2022, 14, 29422-29430.	4.0	3
13	Dimensional crossover in self-intercalated antiferromagnetic $\text{V}_5\text{S}_8$ nanoflakes. <i>Physical Review B</i> , 2022, 105, .	1.1	6
14	Lowering of $T_c$ in Van Der Waals Layered Materials Under In-Plane Strain. <i>IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control</i> , 2021, 68, 253-258.	1.7	3
15	Determination of rutile transition metal oxide (110) surface terminations by scanning tunneling microscopy contrast reversal. <i>Physical Review B</i> , 2021, 103, .	1.1	0
16	Preferential hole defect formation in monolayer $\text{WSe}_2$ by electron-beam irradiation. <i>Physical Review Materials</i> , 2021, 5, .	0.9	4
17	Direct visualization of anionic electrons in an electride reveals inhomogeneities. <i>Science Advances</i> , 2021, 7, .	4.7	24
18	3-D Full-Band Monte Carlo Simulation of Hot-Electron Energy Distributions in Gate-All-Around Si Nanowire MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2021, 68, 2556-2563.	1.6	11

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19	Atomically sharp interface enabled ultrahigh-speed non-volatile memory devices. Nature Nanotechnology, 2021, 16, 882-887.	15.6	105
20	Quantum physical reality of polar-nonpolar oxide heterostructures. Physical Review B, 2021, 104, .	1.1	2
21	Defect and Impurity-Complex Depassivation During Electron-Beam Irradiation of GaAs. IEEE Transactions on Nuclear Science, 2021, 68, 1548-1555.	1.2	2
22	Anisotropic point defects in rhenium diselenide monolayers. IScience, 2021, 24, 103456.	1.9	11
23	Radiation Effects and Low-Frequency Noise in AlGaN/GaN HEMTs. , 2021, , .		0
24	Synthesis and properties of free-standing monolayer amorphous carbon. Nature, 2020, 577, 199-203.	13.7	250
25	Tunable quadruple-well ferroelectric van der Waals crystals. Nature Materials, 2020, 19, 43-48.	13.3	140
26	Total-Ionizing-Dose Effects and Low-Frequency Noise in 16-nm InGaAs FinFETs With HfO <sub>2</sub> /Al <sub>2</sub> O <sub>3</sub> Dielectrics. IEEE Transactions on Nuclear Science, 2020, 67, 210-220.	1.2	26
27	Thermal Conductivity of HfTe <sub>5</sub> : A Critical Revisit. Advanced Functional Materials, 2020, 30, 1907286.	7.8	9
28	Direct Visualization of Hydrogen-Transfer Intermediate States by Scanning Tunneling Microscopy. Journal of Physical Chemistry Letters, 2020, 11, 1536-1541.	2.1	3
29	Piezoelectric domain walls in van der Waals antiferroelectric CuInP <sub>2</sub> Se <sub>6</sub> . Nature Communications, 2020, 11, 3623.	5.8	47
30	Insulating SiO <sub>2</sub> under Centimeter-Scale, Single-Crystal Graphene Enables Electronic-Device Fabrication. Nano Letters, 2020, 20, 8584-8591.	4.5	19
31	Local Strain and Polarization Mapping in Ferrielectric Materials. ACS Applied Materials & Interfaces, 2020, 12, 38546-38553.	4.0	14
32	The Concept of Negative Capacitance in Ionically Conductive Van der Waals Ferroelectrics. Advanced Energy Materials, 2020, 10, 2001726.	10.2	30
33	Doping-driven electronic and lattice dynamics in the phase-change material vanadium dioxide. Physical Review B, 2020, 102, .	1.1	8
34	Ferroelectric-Gated InSe Photodetectors with High On/Off Ratios and Photoresponsivity. Nano Letters, 2020, 20, 6666-6673.	4.5	53
35	Wrinkle-induced highly conductive channels in graphene on SiO <sub>2</sub> /Si substrates. Nanoscale, 2020, 12, 12038-12045.	2.8	11
36	Evidence for Interfacial Octahedral Coupling as a Route to Enhance Magnetoresistance in Perovskite Oxide Superlattices. Advanced Materials Interfaces, 2020, 7, 1901576.	1.9	8

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37	Sizable Band Gap in Epitaxial Bilayer Graphene Induced by Silicene Intercalation. Nano Letters, 2020, 20, 2674-2680.	4.5	23
38	Airâ€Stable Monolayer Cu<sub>2</sub>Se Exhibits a Purely Thermal Structural Phase Transition. Advanced Materials, 2020, 32, e1908314.	11.1	26
39	Tuning the Catalytic Activity of a Quantum Nutcracker for Hydrogen Dissociation. Surfaces, 2020, 3, 40-47.	1.0	2
40	Alignment of Polarization against an Electric Field in van der Waals Ferroelectrics. Physical Review Applied, 2020, 13, .	1.5	34
41	Integration of graphene and two-dimensional ferroelectrics: properties and related functional devices. Nanoscale Horizons, 2020, 5, 1303-1308.	4.1	12
42	Domains and Topological Defects in Layered Ferrielectric Materials: Implications for Nanoelectronics. ACS Applied Nano Materials, 2020, 3, 8161-8166.	2.4	4
43	Unusual anisotropic thermal expansion in multilayer SnSe leads to positive-to-negative crossover of Poisson's ratio. Applied Physics Letters, 2020, 116, 083101.	1.5	2
44	Hafnium Pentatelluride: Thermal Conductivity of HfTe<sub>5</sub>: A Critical Revisit (Adv. Funct.) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50	7.8	0
45	Synthesis of Coâ€Doped MoS<sub>2</sub> Monolayers with Enhanced Valley Splitting. Advanced Materials, 2020, 32, e1906536.	11.1	84
46	InSe/hBN/graphite heterostructure for high-performance 2D electronics and flexible electronics. Nano Research, 2020, 13, 1127-1132.	5.8	48
47	Quantum prediction of ultra-low thermal conductivity in lithium intercalation materials. Nano Energy, 2020, 75, 104916.	8.2	24
48	Detection of defects in atomic-resolution images of materials using cycle analysis. Advanced Structural and Chemical Imaging, 2020, 6, .	4.0	11
49	Defect Dehydrogenation in Si-MOS and Compound-Semiconductor-Based Devices. , 2020, , .		1
50	Electronic Structure and Coupling of Re Clusters In Monolayer MoS2. Microscopy and Microanalysis, 2019, 25, 506-507.	0.2	0
51	Theory of photo-ionization defects in nano-porous SiC alloys. Journal of Applied Physics, 2019, 125, 215703.	1.1	1
52	<i>In</i>-<i>Situ</i> Observation of the Continuous Phase Transition in Determining the High Thermoelectric Performance of Polycrystalline Sn<sub>0.98</sub>Se. Journal of Physical Chemistry Letters, 2019, 10, 6512-6517.	2.1	32
53	Intrinsic interfacial van der Waals monolayers and their effect on the high-temperature superconductor <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" > <mml:msub> <mml:mrow> <mml:mi>FeSe</mml:mi> <mml:mto> </mml:mo> <mml:mi> </mml:mi> </mml:math>	1.1	11
54	Centimeter-scale, single-crystalline, AB-stacked bilayer graphene on insulating substrates. 2D Materials, 2019, 6, 045044.	2.0	11

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55	Atomically precise, custom-design origami graphene nanostructures. <i>Science</i> , 2019, 365, 1036-1040.	6.0	156
56	Origin of Pyroelectricity in Ferroelectric HfO <sub>2</sub> . <i>Physical Review Applied</i> , 2019, 12, .	1.5	37
57	Super Large Sn <sup>x</sup> Se Single Crystals with Excellent Thermoelectric Performance. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 8051-8059.	4.0	43
58	Observation of Square-Planar Distortion in Lanthanide-Doped Skutterudite Crystals. <i>Journal of Physical Chemistry C</i> , 2019, 123, 14632-14638.	1.5	1
59	Defect-Mediated Phase Transformation in Anisotropic Two-Dimensional PdSe <sub>2</sub> Crystals for Seamless Electrical Contacts. <i>Journal of the American Chemical Society</i> , 2019, 141, 8928-8936.	6.6	81
60	Atomic-scale determination of spontaneous magnetic reversal in oxide heterostructures. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2019, 116, 10309-10316.	3.3	18
61	Tunable Thermal Energy Transport across Diamond Membranes and Diamond-Si Interfaces by Nanoscale Graphoepitaxy. <i>ACS Applied Materials &amp; Interfaces</i> , 2019, 11, 18517-18527.	4.0	49
62	Electron Transport Properties of $\text{Al}_x\text{Ga}_{1-x}\text{N}$ Transistors Based on F. <i>Physical Review Applied</i> , 2019, 11, .	2.9	29
63	Spectroscopic signatures of edge states in hexagonal boron nitride. <i>Nano Research</i> , 2019, 12, 1663-1667.	5.8	7
64	Spatially and spectrally resolved orbital angular momentum interactions in plasmonic vortex generators. <i>Light: Science and Applications</i> , 2019, 8, 33.	7.7	25
65	Direct Cation Exchange in Monolayer MoS <sub>2</sub> via Recombination-Enhanced Migration. <i>Physical Review Letters</i> , 2019, 122, 106101.	7.9	21
66	Spontaneous Formation of 1D Pattern in Monolayer VSe <sub>2</sub> with Dispersive Adsorption of Pt Atoms for HER Catalysis. <i>Nano Letters</i> , 2019, 19, 4897-4903.	4.5	42
67	High Thermoelectric Performance in p-type Polycrystalline Cd-doped SnSe Achieved by a Combination of Cation Vacancies and Localized Lattice Engineering. <i>Advanced Energy Materials</i> , 2019, 9, 1803242.	10.2	150
68	Interface-induced magnetic polar metal phase in complex oxides. <i>Nature Communications</i> , 2019, 10, 5248.	5.8	35
69	Strong Phonon-Phonon Interactions Securing Extraordinary Thermoelectric Ge <sup>x</sup> Sb <sup>x</sup> Te with Zn-Alloying-Induced Band Alignment. <i>Journal of the American Chemical Society</i> , 2019, 141, 1742-1748.	6.6	199
70	Understanding the Average Electron-Hole Pair-Creation Energy in Silicon and Germanium Based on Full-Band Monte Carlo Simulations. <i>IEEE Transactions on Nuclear Science</i> , 2019, 66, 444-451.	1.2	16
71	Total Ionizing Dose Effects and Proton-Induced Displacement Damage on MoS <sub>2</sub> -Interlayer-MoS <sub>2</sub> Tunneling Junctions. <i>IEEE Transactions on Nuclear Science</i> , 2019, 66, 420-427.	1.2	6
72	Quantum nutcracker for near-room-temperature H <sub>2</sub> dissociation. <i>Science Bulletin</i> , 2019, 64, 4-7.	4.3	3

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73	Total-Ionizing-Dose Response of MoS <sub>2</sub> Transistors With ZrO <sub>2</sub> and h-BN Gate Dielectrics. IEEE Transactions on Nuclear Science, 2019, 66, 1584-1591.	1.2	6
74	Giant negative electrostriction and dielectric tunability in a van der Waals layered ferroelectric. Physical Review Materials, 2019, 3, . Diffusion-driven ultra-low thermal conductivity in amorphous	0.9	47
75	$\text{N} < \text{b} > \text{O} < \text{mn} > 2 < \text{msub} > < \text{msub} > < \text{mi} > \text{math} > \text{thin}$ films. Physical Review Materials, 2019, 3, .	0.9	18
76	Atomic-resolution visualization and doping effects of complex structures in intercalated bilayer graphene. Physical Review Materials, 2019, 3, .	0.9	10
77	Barrierless On-Surface Metal Incorporation in Phthalocyanine-Based Molecules. Journal of Physical Chemistry C, 2018, 122, 6678-6683.	1.5	11
78	Temperature Measurement by a Nanoscale Electron Probe Using Energy Gain and Loss Spectroscopy. Physical Review Letters, 2018, 120, 095901.	2.9	97
79	Defects and Low-Frequency Noise in Irradiated Black Phosphorus MOSFETs With HfO <sub>2</sub> Gate Dielectrics. IEEE Transactions on Nuclear Science, 2018, 65, 1227-1238.	1.2	39
80	Electron-Beam-Induced Synthesis of Hexagonal 1H-MoSe <sub>2</sub> from Square $\text{I}^2\text{-FeSe}$ Decorated with Mo Adatoms. Nano Letters, 2018, 18, 2016-2020.	4.5	2
81	Wu, Zhang, and Pantelides Reply:. Physical Review Letters, 2018, 120, 039602.	2.9	2
82	Wu, Zhang, and Pantelides Reply:. Physical Review Letters, 2018, 120, 039604.	2.9	2
83	Recovery of edge states of graphene nanoislands on an iridium substrate by silicon intercalation. Nano Research, 2018, 11, 3722-3729.	5.8	10
84	Effect of Material Structure on Photoluminescence of ZnO/MgO Core-Shell Nanowires. ChemNanoMat, 2018, 4, 291-300.	1.5	5
85	Mo-Terminated Edge Reconstructions in Nanoporous Molybdenum Disulfide Film. Nano Letters, 2018, 18, 482-490.	4.5	105
86	Anisotropic Ordering in $1\text{T}^{\prime}2$ Molybdenum and Tungsten Ditelluride Layers Alloyed with Sulfur and Selenium. ACS Nano, 2018, 12, 894-901.	7.3	52
87	Dislocation-driven growth of two-dimensional lateral quantum-well superlattices. Science Advances, 2018, 4, eaap9096.	4.7	38
88	Radiation-Induced Charge Trapping and Low-Frequency Noise of Graphene Transistors. IEEE Transactions on Nuclear Science, 2018, 65, 156-163.	1.2	15
89	Temperature Measurement by a Nanoscale Electron Probe using Energy Gain and Loss Spectroscopy. Microscopy and Microanalysis, 2018, 24, 98-99.	0.2	0
90	Stable Silicene in Graphene/Silicene Van der Waals Heterostructures. Advanced Materials, 2018, 30, e1804650.	11.1	86

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91	<p>licity Alteration and Enhanced Oil Recovery induced by Proximal Adsorption of <math>\text{Na}^+\text{Cl}^-</math> ,</p> <p>Record-Low and Anisotropic Thermal Conductivity of a Quasi-One-Dimensional Bulk <math>\text{ZrTe}_5</math> Single Crystal. ACS Applied Materials &amp; Interfaces, 2018, 10, 40740-40747.</p>	1.5	42
92	Rhenium-Doped and Stabilized $\text{MoS}_2$ Atomic Layers with Basal Plane Catalytic Activity. Advanced Materials, 2018, 30, e1803477.	11.1	164
94	Constructing Highly Porous Thermoelectric Monoliths with High-Performance and Improved Portability from Solution-Synthesized Shape-Controlled Nanocrystals. Nano Letters, 2018, 18, 4034-4039.	4.5	38
95	Mechanisms of Pyroelectricity in Three- and Two-Dimensional Materials. Physical Review Letters, 2018, 120, 207602.	2.9	35
96	Nobler than the Noblest: Noncubic Gold Microcrystallites. Angewandte Chemie - International Edition, 2018, 57, 9018-9022.	7.2	10
97	Fabrication of Millimeter-Scale, Single-Crystal One-Third-Hydrogenated Graphene with Anisotropic Electronic Properties. Advanced Materials, 2018, 30, 1801838.	11.1	19
98	Creating Zipper-Like van der Waals Gap Discontinuity in Low-Temperature-Processed Nanostructured $\text{PbBi}_2\text{Te}_{1+3n}$ : Enhanced Phonon Scattering and Improved Thermoelectric Performance. Angewandte Chemie - International Edition, 2018, 57, 10938-10943.	7.2	11
99	Localization of Yttrium Segregation within YSZ Grain Boundary Dislocation Cores. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1800349.	0.8	10
100	Locally Controlled Cu-Ion Transport in Layered Ferroelectric $\text{CuInP}_2\text{S}_6$ . ACS Applied Materials & Interfaces, 2018, 10, 27188-27194.	4.0	68
101	Tuning the morphology of chevron-type graphene nanoribbons by choice of annealing temperature. Nano Research, 2018, 11, 6190-6196.	5.8	20
102	Nobler than the Noblest: Noncubic Gold Microcrystallites. Angewandte Chemie, 2018, 130, 9156-9160.	1.6	2
103	Rapid Atomic-Resolution Image Analysis: Towards Near-Instant Feedback. Microscopy and Microanalysis, 2018, 24, 538-539.	0.2	0
104	Theory-assisted determination of nano-rippling and impurities in atomic resolution images of angle-mismatched bilayer graphene. 2D Materials, 2018, 5, 041008.	2.0	5
105	Dislocation-Driven Growth of Two-Dimensional Lateral Quantum Well Superlattices. Microscopy and Microanalysis, 2018, 24, 88-89.	0.2	0
106	Direct Imaging of Low-Dimensional Nanostructures. Microscopy and Microanalysis, 2018, 24, 90-91.	0.2	0
107	Multiple Defects Cause Degradation After High Field Stress in AlGaIn/GaN HEMTs. IEEE Transactions on Device and Materials Reliability, 2018, 18, 364-376.	1.5	49
108	Sequence of Silicon Monolayer Structures Grown on a Ru Surface: from a Herringbone Structure to Silicene. Nano Letters, 2017, 17, 1161-1166.	4.5	86

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109	Design of a Hole Trapping Ligand. Nano Letters, 2017, 17, 909-914.	4.5	24
110	Defect-mediated leakage in lithium intercalated bilayer graphene. AIP Advances, 2017, 7, .	0.6	5
111	Molecular Beam Epitaxy of Highly Crystalline Monolayer Molybdenum Disulfide on Hexagonal Boron Nitride. Journal of the American Chemical Society, 2017, 139, 9392-9400.	6.6	167
112	<i>In Situ</i> Observation of Oxygen Vacancy Dynamics and Ordering in the Epitaxial LaCoO <sub>3</sub> System. ACS Nano, 2017, 11, 6942-6949.	7.3	89
113	Intrinsically patterned two-dimensional materials for selective adsorption of molecules and Nanoclusters. Nature Materials, 2017, 16, 717-721.	13.3	150
114	Interface-induced multiferroism by design in complex oxide superlattices. Proceedings of the National Academy of Sciences of the United States of America, 2017, 114, E5062-E5069.	3.3	42
115	Unified band-theoretic description of structural, electronic, and magnetic properties of vanadium dioxide phases. Physical Review B, 2017, 95, .	1.1	40
116	Worst-Case Bias for Proton and 10-keV X-Ray Irradiation of AlGaN/GaN HEMTs. IEEE Transactions on Nuclear Science, 2017, 64, 218-225.	1.2	46
117	Memristive devices from ZnO nanowire bundles and meshes. Applied Physics Letters, 2017, 111, .	1.5	11
118	Formation of Single-atom-thick Copper Oxide Monolayers. Microscopy and Microanalysis, 2017, 23, 1684-1685.	0.2	1
119	A novel Pd <sub>2</sub> Se <sub>3</sub> two-dimensional phase driven by interlayer fusion in layered PdSe <sub>2</sub> . Microscopy and Microanalysis, 2017, 23, 1700-1701.	0.2	1
120	Quantum Many-Body Effects in Defective Transition-Metal-Oxide Superlattices. Journal of Chemical Theory and Computation, 2017, 13, 5604-5609.	2.3	7
121	Fast kinetics of magnesium monochloride cations in interlayer-expanded titanium disulfide for magnesium rechargeable batteries. Nature Communications, 2017, 8, 339.	5.8	304
122	Fundamental Resolution of Difficulties in the Theory of Charged Point Defects in Semiconductors. Physical Review Letters, 2017, 119, 105501.	2.9	25
123	Evidence for Ultralow-Energy Vibrations in Large Organic Molecules. Nano Letters, 2017, 17, 4929-4933.	4.5	11
124	Atomic Resolution STEM-EELS Studies of Defects and Local Structural Distortions in Oxide Interfaces. Microscopy and Microanalysis, 2017, 23, 372-373.	0.2	0
125	Design of Optimally Stable Molecular Coatings for Fe-Based Nanoparticles in Aqueous Environments. ACS Omega, 2017, 2, 4480-4487.	1.6	3
126	Direct Four-Probe Measurement of Grain-Boundary Resistivity and Mobility in Millimeter-Sized Graphene. Nano Letters, 2017, 17, 5291-5296.	4.5	59



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127	Observing Nanoscale Orbital Angular Momentum in Plasmon Vortices with Cathodoluminescence. Microscopy and Microanalysis, 2017, 23, 1694-1695.	0.2	0
128	Engineering an Insulating Ferroelectric Superlattice with a Tunable Band Gap from Metallic Components. Physical Review Letters, 2017, 119, 177603.	2.9	16
129	Structural "Doping" to Control Local Magnetization in Isovalent Oxide Heterostructures. Physical Review Letters, 2017, 119, 197204.	2.9	28
130	Sulfur-doped graphene nanoribbons with a sequence of distinct band gaps. Nano Research, 2017, 10, 3377-3384.	5.8	44
131	Novel $\text{Pd}_2\text{Se}$ Two-Dimensional Phase Driven by Interlayer Fusion in Layered $\text{PdSe}$ . Physical Review Letters, 2017, 119, 016101.	2.9	111
132	Large Area and High Quality 2D Transition Metal Telluride. Advanced Materials, 2017, 29, 1603471.	11.1	181
133	Unsupported single-atom-thick copper oxide monolayers. 2D Materials, 2017, 4, 011001.	2.0	44
134	Near-Field Mid-Infrared Plasmonics in Complex Nanostructures with Monochromated Electron Energy Loss Spectroscopy. Microscopy and Microanalysis, 2017, 23, 1532-1533.	0.2	0
135	Identifying Novel Polar Distortion Modes in Engineered Magnetic Oxide Superlattices. Microscopy and Microanalysis, 2017, 23, 1590-1591.	0.2	1
136	Exchange of Re and Mo atoms in MoS <sub>2</sub> driven by Scanning Transmission Electron Microscopy. Microscopy and Microanalysis, 2017, 23, 1702-1703.	0.2	0
137	Properties of Hydrogenated Nanoporous SiC: An Ab Initio Study. Journal of Nanomaterials, 2017, 2017, 1-6.	1.5	5
138	Oxide Epitaxy with Large Symmetry Mismatch: Bronze-phase VO <sub>2</sub> on SrTiO <sub>3</sub> . Microscopy and Microanalysis, 2017, 23, 1580-1581.	0.2	1
139	Total ionizing dose effects in passivated and unpassivated AlGaIn/GaN HEMTs. , 2016, , .		4
140	Low-Loss Imaging of Defect Structures in Two Dimensional Materials Using Aberration Corrected Scanning Transmission Electron Microscopy. Microscopy and Microanalysis, 2016, 22, 1410-1411.	0.2	0
141	Unveiling Complex Plasmonic Resonances in Archimedean Nanospirals through Cathodoluminescence in a Scanning Transmission Electron Microscope. Microscopy and Microanalysis, 2016, 22, 266-267.	0.2	3
142	Tracking BO 6 Coupling in Perovskite Superlattices to Engineer Magnetic Interface Behavior. Microscopy and Microanalysis, 2016, 22, 904-905.	0.2	0
143	High On/Off Ratio Memristive Switching of Manganite/Cuprate Bilayer by Interfacial Magnetoelectricity. Advanced Materials Interfaces, 2016, 3, 1600086.	1.9	5
144	Synthesis of Millimeter Scale Transition Metal Dichalcogenides Single Crystals. Advanced Functional Materials, 2016, 26, 2009-2015.	7.8	152

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145	High-Field Stress, Low-Frequency Noise, and Long-Term Reliability of AlGaIn/GaN HEMTs. IEEE Transactions on Device and Materials Reliability, 2016, 16, 282-289.	1.5	25
146	MoS <sub>2</sub> /TiO <sub>2</sub> Edge-on Heterostructure for Efficient Photocatalytic Hydrogen Evolution. Advanced Energy Materials, 2016, 6, 1600464.	10.2	264
147	Magnetic Ordering in Sr <sub>3</sub> YCo <sub>4</sub> O <sub>10+x</sub> . Scientific Reports, 2016, 6, 19762.	1.6	9
148	Single Atom Imaging and Spectroscopy of Impurities in 2D Materials. Microscopy and Microanalysis, 2016, 22, 862-863.	0.2	0
149	Degradation and annealing effects caused by oxygen in AlGaIn/GaN high electron mobility transistors. Applied Physics Letters, 2016, 109, .	1.5	22
150	Variability of structural and electronic properties of bulk and monolayer Si <sub>2</sub> Te <sub>3</sub> . Applied Physics Letters, 2016, 109, .	1.5	24
151	Effects of Negative-Bias-Temperature-Instability on Low-Frequency Noise in SiGe $\text{p}$ MOSFETs. IEEE Transactions on Device and Materials Reliability, 2016, 16, 541-548.	1.5	16
152	Implantation and Diffusion of Silicon Marker Layers in In <sub>0.53</sub> Ga <sub>0.47</sub> As. Journal of Electronic Materials, 2016, 45, 4282-4287.	1.0	5
153	Patterned Growth: Patterned Growth of P-Type MoS <sub>2</sub> Atomic Layers Using Sol-Gel as Precursor (Adv. Tj ETQq1 1 0.784314 rgBT /Over 7.8 80)	7.8	34
154	Dual-mode crystal-bound and X-type passivation of quantum dots. Chemical Communications, 2016, 52, 12214-12217.	2.2	21
155	Towards spin-polarized two-dimensional electron gas at a surface of an antiferromagnetic insulating oxide. Physical Review B, 2016, 94, .	1.1	6
156	Patterned Growth of P-Type MoS <sub>2</sub> Atomic Layers Using Sol-Gel as Precursor. Advanced Functional Materials, 2016, 26, 6371-6379.	7.8	34
157	Room-temperature ferroelectricity in CuInP <sub>2</sub> S <sub>6</sub> ultrathin flakes. Nature Communications, 2016, 7, 12357.	5.8	637
158	Two-dimensional GaSe/MoSe <sub>2</sub> misfit bilayer heterojunctions by van der Waals epitaxy. Science Advances, 2016, 2, e1501882.	4.7	239
159	Introduction of Interfacial Charges to Black Phosphorus for a Family of Planar Devices. Nano Letters, 2016, 16, 6870-6878.	4.5	69
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161	Alloying in Flexible Transition-metal Chalcogenide Nanowires. Microscopy and Microanalysis, 2016, 22, 1424-1425.	0.2	0
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